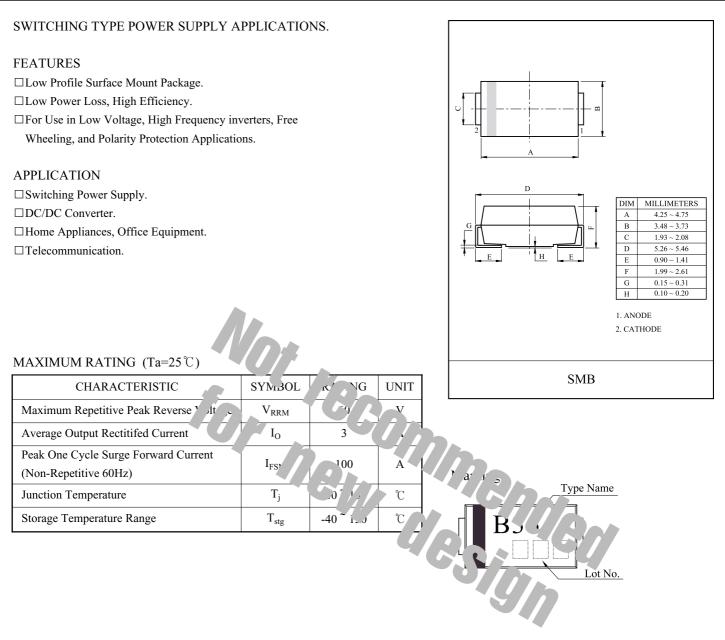


SEMICONDUCTOR TECHNICAL DATA

SMBB36

SCHOTTKY BARRIER TYPE DIODE



ELECTRICAL CHARACTERISTICS (Ta=25°C)

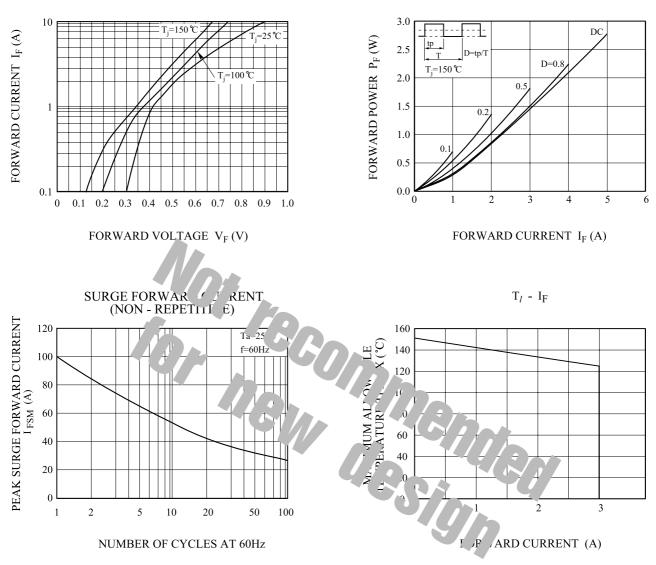
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Peak Forward Voltage	V _{FM}	I _{FM} =3.0A	-	-	0.65	V
Repetitive Peak Reverse Current	I _{RRM}	V _{RRM} =Rated, Tj=25 °C	-	-	0.1	mA
		V _{RRM} =Rated, Tj=100℃	-	-	10	mA
Total Capacitance	CT	V _R =4V, f=1MHz	-	-	250	pF
Thermal Resistance	R _{th(j-1)}	Junction to lead	-	-	15	°C/W

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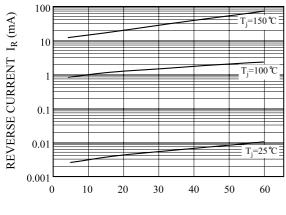
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 P_F - I_F





$$I_R$$
 - V_R



REVERSE VOLTAGE $V_R(V)$

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